

NX3020NAKV

30 V, 200 mA dual N-channel Trench MOSFET

29 October 2013

Product data sheet

1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a ultra small and flat lead SOT666 Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Very fast switching
- Trench MOSFET technology
- ESD protection
- Low threshold voltage

3. Applications

- · Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	or						
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	30	V
V _{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	-	200	mA
Static chara	cteristics (per transistor)						
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_{D} = 100 mA; T_{j} = 25 °C		-	2.7	4.5	Ω

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1	6 5 4	D1 D2
2	G1	gate TR1		
3	D2	drain TR2		G1 $G2$ $G2$
4	S2	source TR2	1 2 3	
5	G2	gate TR2	SOT666	
6	D1	drain TR1		S1 S2 017aaa256

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
NX3020NAKV	SOT666	plastic surface-mounted package; 6 leads	SOT666		

7. Marking

Table 4. Marking codes

Type number	Marking code
NX3020NAKV	GB

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit		
Per transistor								
V _{DS}	drain-source voltage	T _j = 25 °C		-	30	V		
V_{GS}	gate-source voltage			-20	20	V		
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	200	mA		
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	120	mA		
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10$ μs		-	800	mA		
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	260	mW		
			[1]	-	370	mW		
		T _{sp} = 25 °C		-	1100	mW		

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Symbol	Parameter	Conditions		Min	Max	Unit			
Source-drain	Source-drain diode								
I _S	source current	T _{amb} = 25 °C		-	200	mA			
Per device	Per device								
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	375	mW			
T _j	junction temperature			-55	150	°C			
T _{amb}	ambient temperature			-55	150	°C			
T _{stg}	storage temperature			-65	150	°C			

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

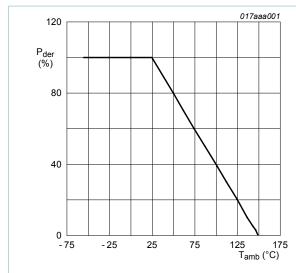


Fig. 1. Normalized total power dissipation as a function of ambient temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

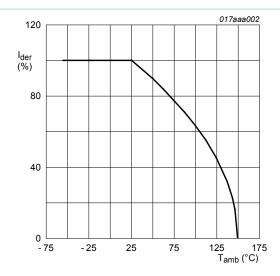


Fig. 2. Normalized continuous drain current as a function of ambient temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$

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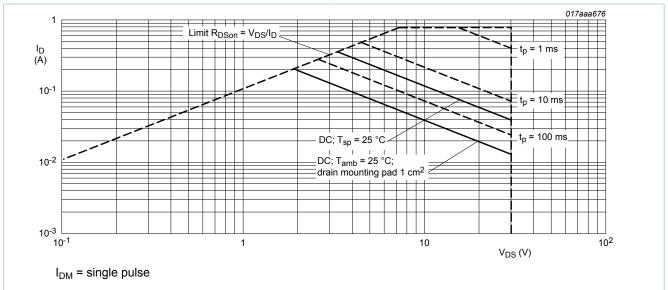


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor			1				_
R _{th(j-a)} thermal resistance from junction to ambient		in free air	[1]	-	410	480	K/W
	_		[2]	-	290	340	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	105	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

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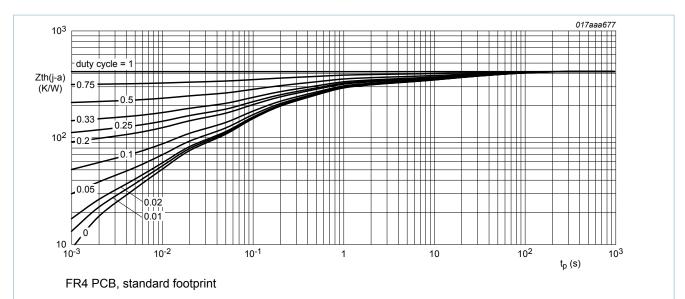


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

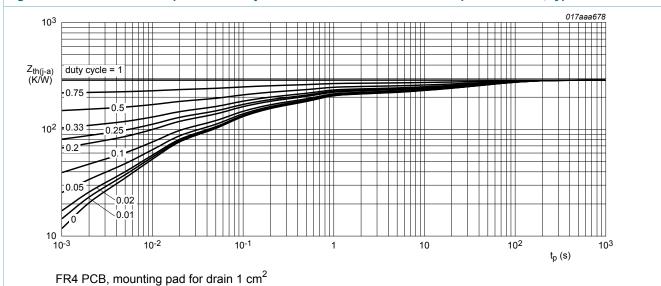


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics (per transistor)		'			
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 μ A; V_{GS} = 0 V; T_j = 25 °C	30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \ \mu\text{A}; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}\text{C}$	8.0	1.2	1.5	V
I _{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μA
		V _{DS} = 30 V; V _{GS} = 0 V; T _j = 150 °C	-	-	10	μA
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	3.5	μΑ
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	3.5	μΑ
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μA
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μA
		V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	0.5	μA
		$V_{GS} = -4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	0.5	μA
R _{DSon}	drain-source on-state	V_{GS} = 10 V; I_D = 100 mA; T_j = 25 °C	-	2.7	4.5	Ω
	resistance	V _{GS} = 10 V; I _D = 100 mA; T _j = 150 °C	-	5.5	9.2	Ω
		V _{GS} = 4.5 V; I _D = 100 mA; T _j = 25 °C	-	3	5.2	Ω
		$V_{GS} = 2.5 \text{ V}; I_D = 10 \text{ mA}; T_j = 25 ^{\circ}\text{C}$	-	4	13	Ω
9 _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 150 mA; T _j = 25 °C	-	320	-	mS
Dynamic c	haracteristics (per transist	or)	· ·	'	'	
Q _{G(tot)}	total gate charge	V _{DS} = 15 V; I _D = 150 mA; V _{GS} = 4.5 V;	-	0.34	0.44	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.11	-	nC
Q_{GD}	gate-drain charge		-	0.06	-	nC
C _{iss}	input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V;	-	13	20	pF
C _{oss}	output capacitance	T _j = 25 °C	-	2.6	-	pF
C _{rss}	reverse transfer capacitance		-	1.1	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 20 V; R_L = 250 Ω ; V_{GS} = 10 V;	-	5	10	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega$; $T_j = 25 °C$	-	5	-	ns
t _{d(off)}	turn-off delay time		-	34	68	ns
t _f	fall time		-	17	-	ns
Source-dra	in diode (per transistor)				1	
V_{SD}	source-drain voltage	I_S = 115 mA; V_{GS} = 0 V; T_j = 25 °C	0.47	0.7	1.2	V

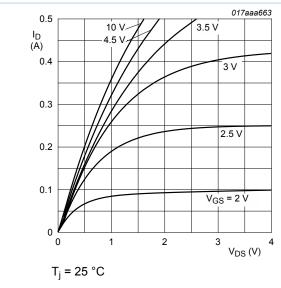


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

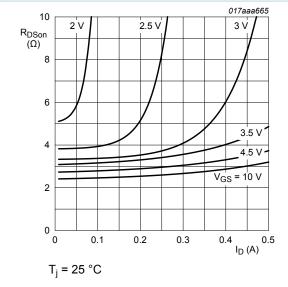


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

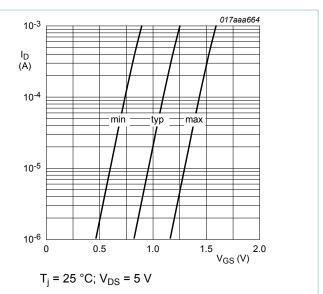


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

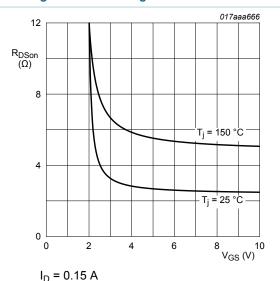


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

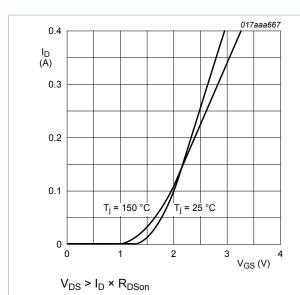


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

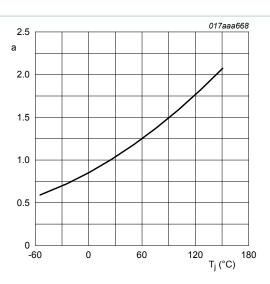


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

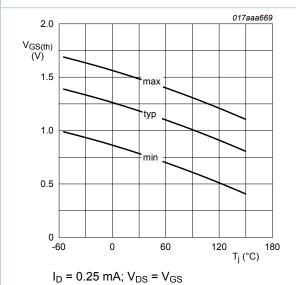
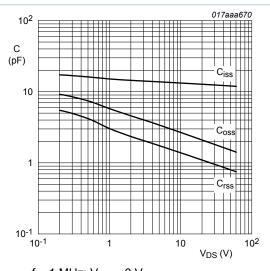


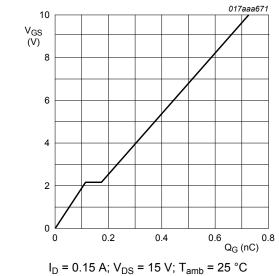
Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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charge; typical values

I_D = 0.15 A; V_{DS} = 15 V; T_{amb} = 25 °C Fig. 14. Gate-source voltage as a function of gate

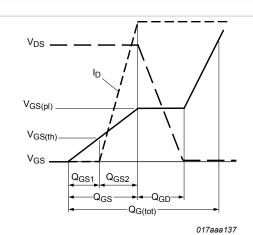


Fig. 15. Gate charge waveform definitions

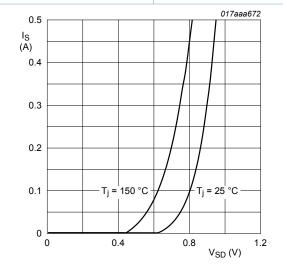
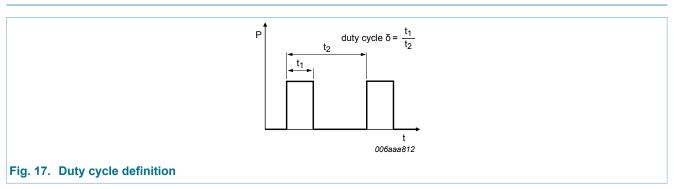


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$



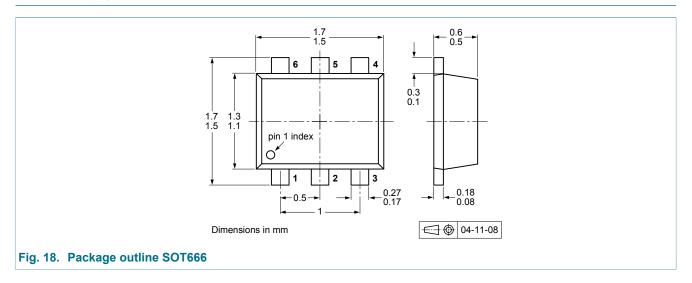
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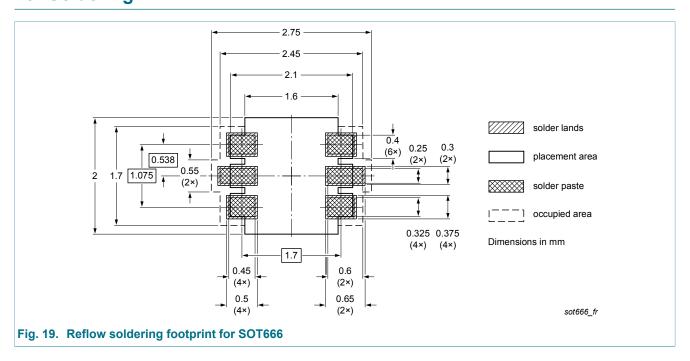
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12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
NX3020NAKV v.2	20131029	Product data sheet	-	NX3020NAKV v.1		
Modifications:	 3D package outline added Table 7 values of capacitance parameters corrected Figure 13 corrected 					
NX3020NAKV v.1	20120706	Product data sheet	-	-		

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Document status [1][2]	Product status [3]	Definition
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Product [short] data sheet	Production	This document contains the product specification.

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